



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

MUN2232

## SOT-23 Digital Transistor 数字晶体管

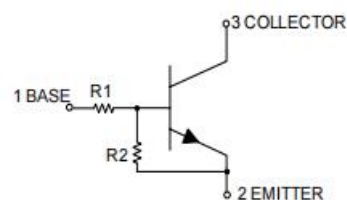
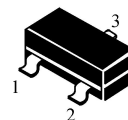
### ■ Features 特点

NPN With Bias Resistor Network  
带偏置电阻

### ■ Absolute Maximum Ratings 最大额定值

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	50	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	50	V
Collector Current 集电极电流	$I_C$	100	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	246	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	508	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^\circ\text{C}$	

### ■ Device Marking 产品打标

MUN2232=A8J

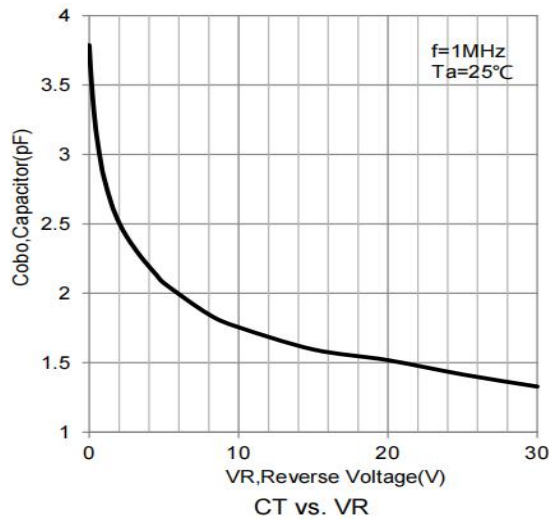
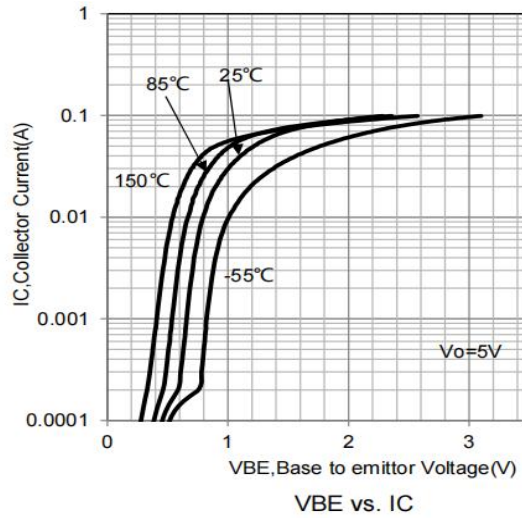
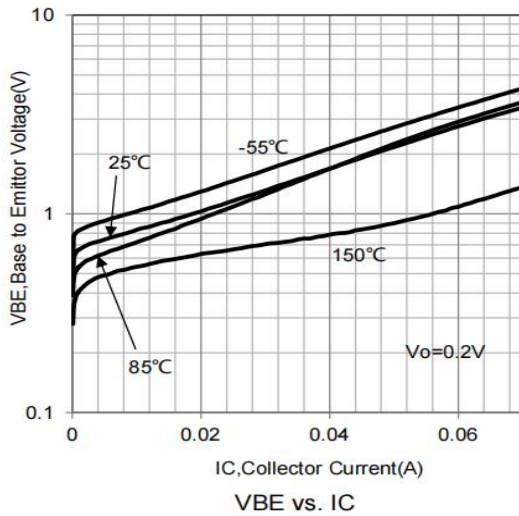
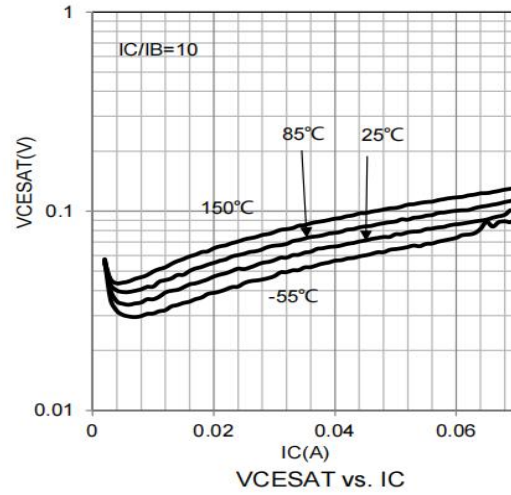
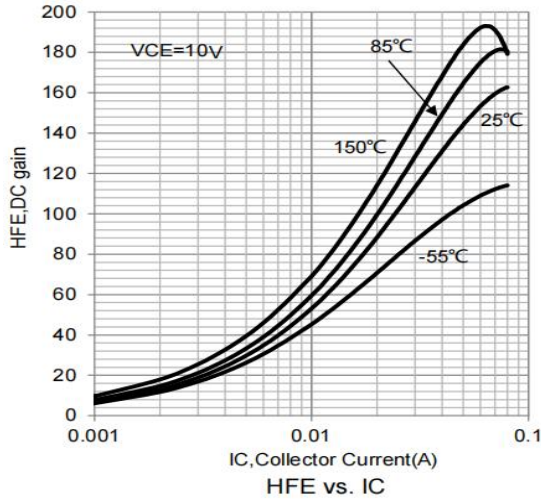


## ■ Electrical Characteristics 电特性

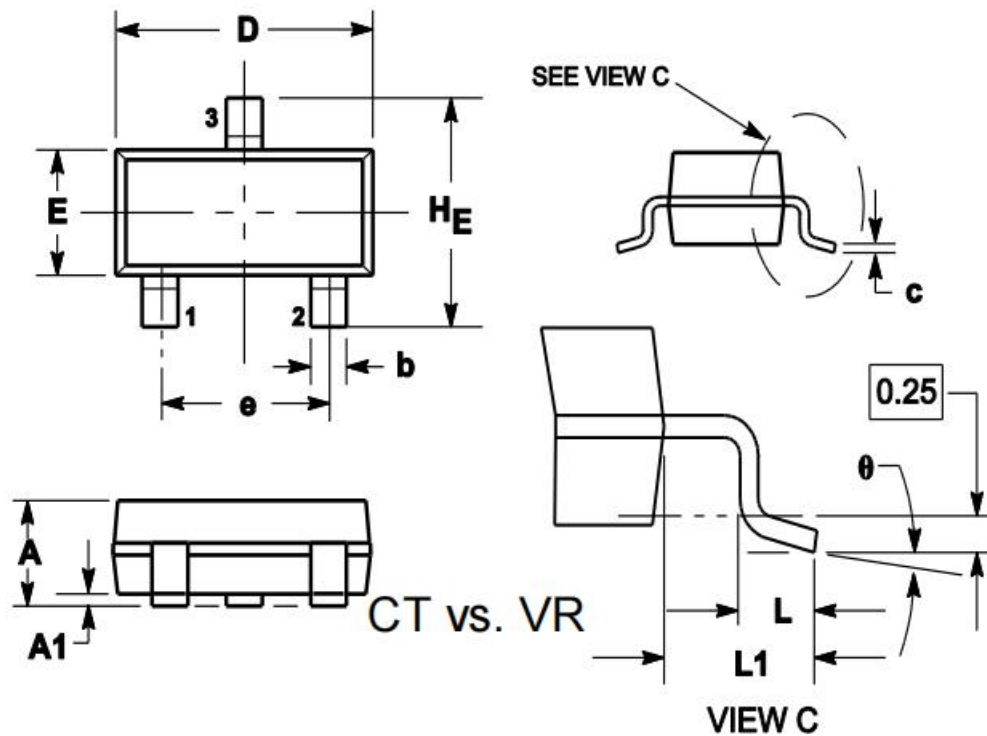
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压 ( $I_C=10\mu\text{A}$ , $I_E=0$ )	$BV_{CBO}$	50	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压 ( $I_C=2\text{mA}$ , $I_B=0$ )	$BV_{CEO}$	50	—	—	V
Collector-Base Leakage Current 集电极基极漏电流 ( $V_{CB}=50\text{V}$ , $I_E=0$ )	$I_{CBO}$	—	—	50	nA
Collector-Emitter Leakage Current 集电极发射极漏电流 ( $V_{CE}=50\text{V}$ , $I_E=0$ )	$I_{CEO}$	—	—	50	nA
Emitter-Base Leakage Current 发射极基极漏电流 ( $V_{EB}=6\text{V}$ , $I_C=0$ )	$I_{EBO}$	—	—	1.5	mA
DC Current Gain 直流电流增益 ( $V_{CE}=10\text{V}$ , $I_C=5\text{mA}$ )	$H_{FE}$	15	30	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ( $I_C=10\text{mA}$ , $I_B=1\text{mA}$ )	$V_{CE(sat)}$	—	—	0.25	V
Output Voltage (on) 输出电压(导通) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 2.5\text{ V}$ , $R_L = 1.0\text{K}\Omega$ )	$V_{OL}$	—	—	0.2	V
Output Voltage (on) 输出电压(导通) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 0.25\text{ V}$ , $R_L = 1.0\text{K}\Omega$ )	$V_{OH}$	4.9	—	—	V
Input Resistor 输入电阻	R1	3.3	4.7	6.1	$\text{K}\Omega$
Resistor Ratio 电阻比率	R1/R2	0.8	1	1.2	

## ■ Typical Characteristic Curve 典型特性曲线



## Dimension 外形封装尺寸



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°